

Surface and Thin Film Analysis

Principles, Instrumentation, Applications

Edited by H. Bubert and H. Jenett

Contents

Preface XIII

List of Authors XV

1	Introduction	1
	<i>John C. Rivière and Henning Bubert</i>	
2	Electron Detection	6
2.1	Photoelectron Spectroscopy	6
	<i>H. Bubert and J. C. Rivière</i>	
2.1.1	Principles	6
2.1.2	Instrumentation	9
2.1.2.1	Vacuum Requirement	9
2.1.2.2	X-ray Sources	10
2.1.2.3	Synchrotron Radiation	12
2.1.2.4	Electron-energy Analyzer (CHA)	13
2.1.2.5	Spatial Resolution	14
2.1.3	Spectral Information and Chemical Shift	15
2.1.4	Quantification, Depth Profiling and Imaging	17
2.1.4.1	Quantification	17
2.1.4.2	Depth Profiling	18
2.1.4.3	Imaging	21
2.1.5	The Auger Parameter	22
2.1.6	Applications	23
2.1.6.1	Catalysis	23
2.1.6.2	Polymers	25
2.1.6.3	Corrosion and Passivation	25
2.1.6.4	Adhesion	27
2.1.6.5	Superconductors	28
2.1.6.6	Interfaces	30
2.1.7	Ultraviolet Photoelectron Spectroscopy (UPS)	32

2.2	Auger Electron Spectroscopy (AES)	32
	<i>H. Bubert and J. C. Rivière</i>	
2.2.1	Principles	33
2.2.2	Instrumentation	33
2.2.2.1	Vacuum Requirement	33
2.2.2.2	Electron Sources	34
2.2.2.3	Electron-energy Analyzer (CMA)	35
2.2.3	Spectral Information	36
2.2.4	Quantification and Depth Profiling	40
2.2.4.1	Quantification	40
2.2.4.2	Depth Profiling	42
2.2.5	Applications	42
2.2.5.1	Grain Boundary Segregation	42
2.2.5.2	Semiconductor Technology	44
2.2.5.3	Thin Films and Interfaces	45
2.2.5.4	Surface Segregation	47
2.2.6	Scanning Auger Microscopy (SAM)	48
2.3	Electron Energy-loss Spectroscopy (EELS)	50
	<i>R. Schneider</i>	
2.3.1	Principles	51
2.3.2	Instrumentation	52
2.3.3	Qualitative Spectral Information	55
2.3.3.1	Low-loss Excitations	57
2.3.3.2	Ionization Losses	59
2.3.3.3	Fine Structures	62
2.3.4	Quantification	65
2.3.5	Imaging of Element Distribution	67
2.3.6	Summary	70
2.4	Low-energy Electron Diffraction (LEED)	71
	<i>G. Held</i>	
2.4.1	Principles and History	71
2.4.2	Instrumentation	72
2.4.3	Qualitative Information	73
2.4.3.1	LEED Pattern	74
2.4.3.2	Spot-profile Analysis	76
2.4.3.3	Applications and Restrictions	78
2.4.4	Quantitative Information	79
2.4.4.1	Principles	79
2.4.4.2	Experimental Techniques	80
2.4.4.3	Computer Programs	81
2.4.4.4	Applications and Restrictions	82

2.5	Other Electron-detecting Techniques	83
	<i>J. C. Rivière</i>	
2.5.1	Auger Electron Appearance Potential Spectroscopy (AEAPS)	83
2.5.2	Ion (Excited) Auger Electron Spectroscopy (IAES)	83
2.5.3	Ion Neutralization Spectroscopy (INS)	83
2.5.4	Metastable Quenching Spectroscopy (MQS)	84
2.5.5	Inelastic Electron Tunneling Spectroscopy (IETS)	84
3	Ion Detection	86
3.1	Static Secondary Ion Mass Spectrometry (SSIMS)	86
	<i>H. F. Arlinghaus</i>	
3.1.1	Principles	86
3.1.2	Instrumentation	88
3.1.2.1	Ion Sources	88
3.1.2.2	Mass Analyzers	89
3.1.2.2.1	Quadrupole Mass Spectrometers	89
3.1.2.2.2	Time-of-flight Mass Spectrometers	90
3.1.3	Quantification	92
3.1.4	Spectral Information	94
3.1.5	Applications	96
3.1.5.1	Oxide Films	96
3.1.5.2	Interfaces	98
3.1.5.3	Polymers	100
3.1.5.4	Biosensors	101
3.1.5.5	Surface Reactions	103
3.1.5.6	Imaging	104
3.1.5.7	Ultra-shallow Depth Profiling	105
3.2	Dynamic Secondary Ion Mass Spectrometry (SIMS)	106
	<i>H. Hutter</i>	
3.2.1	Principles	106
3.2.2	Instrumentation	108
3.2.2.1	Ion Sources	108
3.2.2.2	Mass Analyzers	109
3.2.3	Spectral Information	111
3.2.4	Quantification	112
3.2.4.1	Relative Sensitivity Factors	112
3.2.4.2	Implantation Standards	112
3.2.4.3	MCs ⁺ Ions	113
3.2.5	Mass Spectra	113
3.2.6	Depth Profiles	115
3.2.7	Imaging	116
3.2.7.1	Scanning SIMS	116
3.2.7.2	Direct Imaging Mode	117

- 3.2.8 3D-SIMS 118
- 3.2.9 Applications 119
 - 3.2.9.1 Implantation Profiles 119
 - 3.2.9.2 Layer Analysis 119
 - 3.2.9.3 3D Trace Element Distribution 120
- 3.3 Electron-impact (EI) Secondary Neutral Mass Spectrometry (SNMS) 122**
H. Jenett
 - 3.3.1 General Principles of SNMS 122
 - 3.3.2 Principles of Electron-beam and HF-Plasma SNMS 123
 - 3.3.3 Instrumentation 125
 - 3.3.4 Spectral Information 127
 - 3.3.5 Quantification 128
 - 3.3.6 Element Depth Profiling 130
 - 3.3.7 Applications 131
- 3.4 Laser-SNMS 132**
H. F. Arlinghaus
 - 3.4.1 Principles 132
 - 3.4.1.1 Non-resonant Laser-SNMS 132
 - 3.4.1.2 Resonant Laser-SNMS 132
 - 3.4.1.3 Experimental Setup 133
 - 3.4.1.4 Ionization Schemes 133
 - 3.4.2 Instrumentation 135
 - 3.4.3 Spectral Information 135
 - 3.4.4 Quantification 135
 - 3.4.5 Applications 136
 - 3.4.5.1 Non-resonant Laser-SNMS 136
 - 3.4.5.2 Resonant Laser-SNMS 139
- 3.5 Rutherford Back-scattering Spectroscopy (RBS) 141**
L. Palmetshofer
 - 3.5.1 Principles 141
 - 3.5.2 Instrumentation 144
 - 3.5.3 Spectral Information 144
 - 3.5.4 Quantification 146
 - 3.5.5 Applications 147
- 3.6 Low-energy Ion Scattering (LEIS) 150**
P. Bauer
 - 3.6.1 Principles 150
 - 3.6.2 Instrumentation 152
 - 3.6.3 Information 154
 - 3.6.3.1 Energy Information 154
 - 3.6.3.2 Yield Information 155

- 3.6.4 Quantification 156
- 3.6.5 Applications 157

- 3.7 Elastic Recoil Detection Analysis (ERDA) 160**
O. Benka
 - 3.7.1 Introduction 160
 - 3.7.2 Fundamentals 162
 - 3.7.3 Particle Identification Methods 164
 - 3.7.4 Equipment 165
 - 3.7.5 Data Analysis 166
 - 3.7.6 Sensitivity and Depth Resolution 166
 - 3.7.7 Applications 167

- 3.8 Nuclear Reaction Analysis (NRA) 170**
O. Benka
 - 3.8.1 Introduction 170
 - 3.8.2 Principles 171
 - 3.8.3 Equipment and Depth Resolution 173
 - 3.8.4 Applications 175

- 3.9 Other Ion-detecting Techniques 177**
J. C. Rivière
 - 3.9.1 Desorption Methods 177
 - 3.9.1.1 Electron Stimulated Desorption (ESD) and Electron Stimulated Desorption Ion Angular Distribution (ESDIAD) 177
 - 3.9.1.2 Thermal Desorption Spectroscopy (TDS) 178
 - 3.9.2 Glow-discharge Mass Spectroscopy (GDMS) 178
 - 3.9.3 Fast-atom Bombardment Mass Spectrometry (FABMS) 179
 - 3.9.4 Atom Probe Microscopy 179
 - 3.9.4.1 Atom Probe Field Ion Microscopy (APFIM) 180
 - 3.9.4.2 Position-sensitive Atom Probe (POSAP) 180

- 4 Photon Detection 181**
 - 4.1 Total Reflection X-ray Fluorescence Analysis (TXRF) 181**
L. Fabry and S. Pahlke
 - 4.1.1 Principles 181
 - 4.1.2 Instrumentation 184
 - 4.1.3 Spectral Information 187
 - 4.1.4 Quantification 188
 - 4.1.5 Applications 189
 - 4.1.5.1 Particulate and Film-type Surface Contamination 189
 - 4.1.5.2 Semiconductors 189
 - 4.1.5.2.1 Depth Profiling by TXRF and Multilayer Structures 191
 - 4.1.5.2.2 Vapor Phase Decomposition (VPD) and Droplet Collection 192

4.2	Energy-dispersive X-ray Spectroscopy (EDXS)	194
	<i>R. Schneider</i>	
4.2.1	Principles	194
4.2.2	Practical Aspects of X-ray Microanalysis and Instrumentation	196
4.2.3	Qualitative Spectral Information	202
4.2.4	Quantification	204
4.2.5	Imaging of Element Distribution	206
4.2.6	Summary	207
4.3	Grazing Incidence X-ray Methods for Near-surface Structural Studies	208
	<i>P. N. Gibson</i>	
4.3.1	Principles	208
4.3.1.1	Glancing Angle X-ray Geometry	208
4.3.1.2	Grazing Incidence X-ray Reflectivity (GXRR)	210
4.3.1.3	Glancing Angle X-ray Diffraction	211
4.3.1.4	ReflEXAFS	213
4.3.2	Experimental Techniques and Data Analysis	214
4.3.2.1	Grazing Incidence X-ray Reflectivity (GXRR)	214
4.3.2.2	Grazing Incidence Asymmetric Bragg (GIAB) Diffraction	215
4.3.3	Applications	217
4.3.3.1	Grazing Incidence X-ray Reflectivity (GXRR)	217
4.3.3.2	Grazing Incidence Asymmetric Bragg (GIAB) Diffraction	218
4.3.3.3	Grazing Incidence X-ray Scattering (GIXS)	220
4.3.3.4	ReflEXAFS	220
4.4	Glow Discharge Optical Emission Spectroscopy (GD-OES)	221
	<i>A. Quentmeier</i>	
4.4.1	Principles	221
4.4.2	Instrumentation	222
4.4.2.1	Glow Discharge Sources	222
4.4.2.2	Spectrometer	224
4.4.2.3	Signal Acquisition	224
4.4.3	Spectral Information	225
4.4.4	Quantification	225
4.4.5	Depth Profiling	226
4.4.6	Applications	228
4.4.6.1	dc GD Sources	228
4.4.6.2	rf GD Sources	230
4.5	Surface Analysis by Laser Ablation	231
	<i>M. Bolshov</i>	
4.5.1	Introduction	231
4.5.2	Instrumentation	232
4.5.2.1	Types of Lasers	232

- 4.5.2.2 Different Schemes of Laser Ablation 233
- 4.5.3 Depth Profiling 235
- 4.5.4 Conclusion 239

- 4.6 Ion Beam Spectrochemical Analysis (IBSCA) 240**
V. Rupertus
- 4.6.1 Principles 241
- 4.6.2 Instrumentation 242
- 4.6.3 Spectral and Analytical Information 243
- 4.6.4 Quantitative Analysis 244
- 4.6.5 Applications 246

- 4.7 Reflection Absorption IR Spectroscopy (RAIRS) 249**
K. Hinrichs
- 4.7.1 Instrumentation 249
- 4.7.2 Principles 250
- 4.7.3 Applications 251

- 4.8 Surface-enhanced Raman Scattering (SERS) 254**
W. Hill
- 4.8.1 Principles 254
- 4.8.2 Surface-Enhanced Raman Scattering (SERS) 256
- 4.8.3 Instrumentation 257
- 4.8.4 Spectral Information 259
- 4.8.5 Quantification 259
- 4.8.6 Applications 260
- 4.8.6.1 Unenhanced Raman Spectroscopy at Smooth Surfaces 260
- 4.8.6.2 Porous Materials 261
- 4.8.6.3 SERS 262
- 4.8.6.4 Near-Field Raman Spectroscopy 263
- 4.8.7 Non-linear Optical Spectroscopy 264

- 4.9 UV-Vis-IR Ellipsometry (ELL) 265**
B. Gruska and A. Röseler
- 4.9.1 Principles 265
- 4.9.2 Instrumentation 267
- 4.9.3 Applications 269
- 4.9.3.1 UV-Vis-NIR Spectral Range 269
- 4.9.3.2 Infrared Ellipsometry 271

- 4.10 Other Photon-detecting Techniques 274**
J. C. Rivière
- 4.10.1 Appearance Potential Methods 274
- 4.10.1.1 Soft X-ray Appearance Potential Spectroscopy (SXAPS) 274
- 4.10.1.2 Disappearance Potential Spectroscopy (DAPS) 275

4.10.2	Inverse Photoemission Spectroscopy (IPES) and Bremsstrahlung Isochromat Spectroscopy (BIS)	275
5	Scanning Probe Microscopy	276
5.1	Atomic Force Microscopy (AFM)	277
	<i>G. Friedbacher</i>	
5.1.1	Principles	277
5.1.2	Instrumentation	279
5.1.3	Applications	281
5.2	Scanning Tunneling Microscopy (STM)	284
	<i>G. Friedbacher</i>	
5.2.1	Principles	284
5.2.2	Instrumentation	286
5.2.3	Lateral and Spectroscopic Information	287
5.2.4	Applications	288
6	Summary and Comparison of Techniques	291
7	Surface and Thin Film Analytical Equipment Suppliers	295
	References	303
	Index	325